

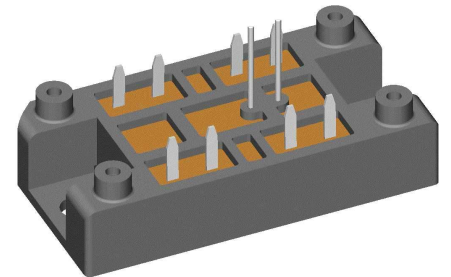
Standard Rectifier Module

3~ Rectifier	Brake Chopper
$V_{RRM} = 1200\text{ V}$	$V_{CES} = 1200\text{ V}$
$I_{DAV} = 75\text{ A}$	$I_{C25} = 58\text{ A}$
$I_{FSM} = 600\text{ A}$	$V_{CE(sat)} = 1.85\text{ V}$

3~ Rectifier Bridge + Brake Unit + NTC

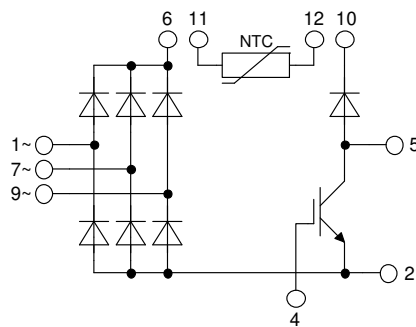
Part number

VUB72-12NOXT



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic base plate
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current
- NTC

Applications:

- 3~ Rectifier with brake unit for drive inverters

Package: V1-A-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 17 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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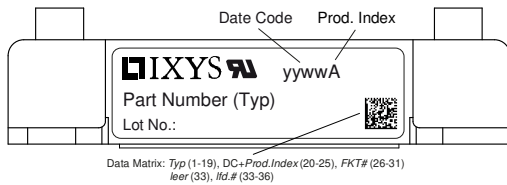
Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					1300	V
V_{RRM}	max. repetitive reverse blocking voltage					1200	V
I_R	reverse current	$V_R = 1200$ V		$T_{VJ} = 25^\circ\text{C}$		40	μA
		$V_R = 1200$ V		$T_{VJ} = 150^\circ\text{C}$		1.5	mA
V_F	forward voltage drop	$I_F = 25$ A		$T_{VJ} = 25^\circ\text{C}$		1.10	V
		$I_F = 75$ A				1.38	V
		$I_F = 25$ A		$T_{VJ} = 125^\circ\text{C}$		1.01	V
		$I_F = 75$ A				1.37	V
I_{DAV}	bridge output current	$T_C = 110^\circ\text{C}$		$T_{VJ} = 150^\circ\text{C}$		75	A
		rectangular	$d = \frac{1}{3}$				
V_{FO}	threshold voltage			$T_{VJ} = 150^\circ\text{C}$		0.79	V
r_F	slope resistance					7.7	m Ω
R_{thJC}	thermal resistance junction to case					1.1	K/W
R_{thCH}	thermal resistance case to heatsink				0.3		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		110	W
I_{FSM}	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		600	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		650	A
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		510	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		550	A
I^2t	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		1.80	kA ² s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		1.76	kA ² s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		1.30	kA ² s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		1.26	kA ² s
C_J	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		19	pF



Brake IGBT				Ratings					
Symbol	Definition	Conditions	min.	typ.	max.	Unit			
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V			
V_{GES}	max. DC gate voltage				± 20	V			
V_{GEM}	max. transient gate emitter voltage				± 30	V			
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			58	A			
I_{C80}		$T_C = 80^{\circ}\text{C}$			40	A			
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			195	W			
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 35\text{ A}; V_{GE} = 15\text{ V}$			1.85	V			
					2.15	V			
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 2\text{ mA}; V_{GE} = V_{CE}$	5.4	5.9	6.5	V			
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$			0.1	mA			
					0.1	mA			
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			500	nA			
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 35\text{ A}$			110	nC			
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 35\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 27\ \Omega$							
t_r	current rise time						$T_{VJ} = 125^{\circ}\text{C}$	70	ns
$t_{d(off)}$	turn-off delay time						40	ns	
t_f	current fall time						250	ns	
E_{on}	turn-on energy per pulse						100	ns	
E_{off}	turn-off energy per pulse						3.8	mJ	
E_{off}		4.1	mJ						
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 27\ \Omega$							
I_{CM}		$V_{CEK} = 1200\text{ V}$			105	A			
SCSOA	short circuit safe operating area	$V_{CEK} = 1200\text{ V}$							
t_{SC}	short circuit duration	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15$			10	μs			
I_{SC}	short circuit current	$R_G = 27\ \Omega$; non-repetitive			140	A			
R_{thJC}	thermal resistance junction to case				0.65	K/W			
R_{thCH}	thermal resistance case to heatsink				0.25	K/W			
Brake Diode									
V_{RRM}	max. repetitive reverse voltage				1200	V			
I_{F25}	forward current				31	A			
I_{F80}					21	A			
V_F	forward voltage	$I_F = 25\text{ A}$			2.97	V			
					2.43	V			
I_R	reverse current	$V_R = V_{RRM}$			0.1	mA			
					0.5	mA			
Q_{rr}	reverse recovery charge	$V_R = 600\text{ V}$ $-di_f/dt = 400\text{ A}/\mu\text{s}$ $I_F = 25\text{ A}; V_{GE} = 0\text{ V}$							
I_{RM}	max. reverse recovery current						$T_{VJ} = 125^{\circ}\text{C}$	1.2	μC
t_{rr}	reverse recovery time						18	A	
R_{thJC}	thermal resistance junction to case				1.6	K/W			
R_{thCH}	thermal resistance case to heatsink				0.55	K/W			



Package V1-A-Pack				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I_{RMS}	RMS current	per terminal			100	A	
T_{VJ}	virtual junction temperature		-40		150	°C	
T_{op}	operation temperature		-40		125	°C	
T_{stg}	storage temperature		-40		125	°C	
Weight				37		g	
M_D	mounting torque		2		2.5	Nm	
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm	
$d_{Spb/Apb}$		terminal to backside	12.0			mm	
V_{ISOL}	isolation voltage	t = 1 second 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3600			V	
		t = 1 minute	3000			V	



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUB72-12NOXT	VUB72-12NOXT	Blister	24	515901

Similar Part	Package	Voltage class
VUB72-16NOXT	V1-A-Pack	1600

Temperature Sensor NTC

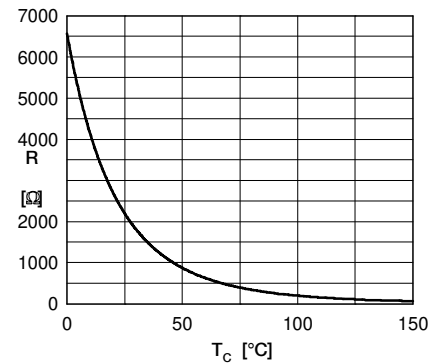
Symbol	Definition	Conditions	min.	typ.	max.	Unit
R_{25}	resistance	$T_{VJ} = 25^\circ$	2.13	2.2	2.27	kΩ
$B_{25/50}$	temperature coefficient			3560		K

Equivalent Circuits for Simulation

* on die level

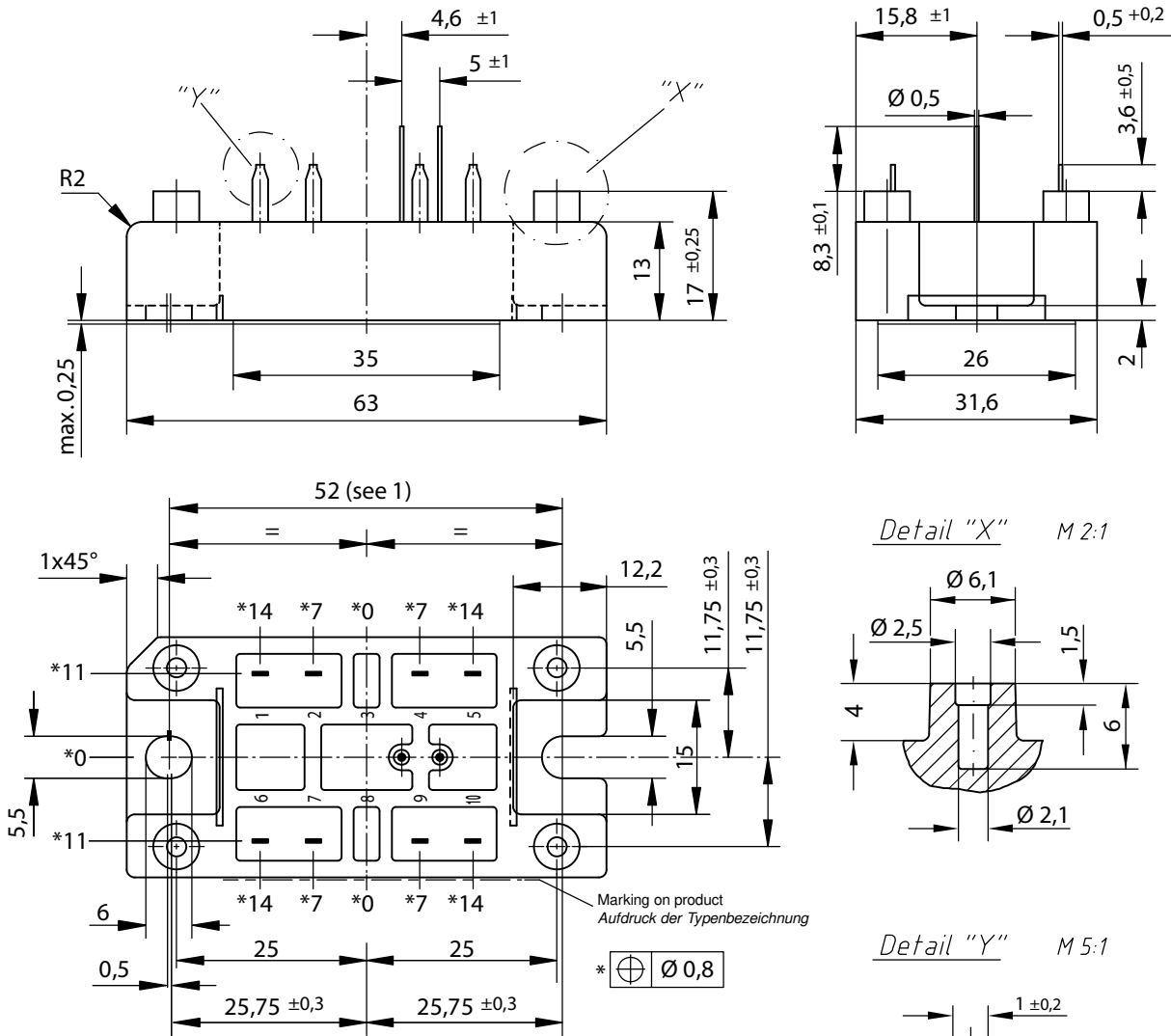
$T_{VJ} = 150^\circ\text{C}$

		Rectifier	Brake IGBT	Brake Diode	
V_0	threshold voltage	0.79	1.1	1.16	V
R_0	slope resistance *	6.5	40	43	mΩ



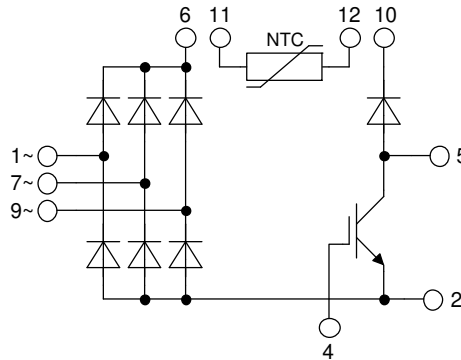


Outlines V1-A-Pack



Remarks / Bemerkungen:

1. Nominal distance mounting screws on heat sink: 52 mm / Nennabstand Befestigungsschrauben auf Kühlkörper: 52 mm
2. General tolerance / Allgmeintoleranz: DIN ISO 2768 - T1-c
3. Surface treatment of pins: tin plated (Sn) in hot dip / Oberflächenbehandlung der Pins: verzinkt (Sn) im Tauchbad
4. **Detail X:**
EJOT PT® self-tapping screws (dimension K25) to be recommended for mounting on PCB
selbstschneidende Schraube (Größe K25) empfohlen für die PCB-Montage
Take care on the maximum screw length according to board thickness and the maximum hole depth of 6 mm⁻¹
Bei der Wahl der Schraubenlänge die PCB-Dicke und die maximale Lochtiefe von 6mm beachten
Recommended mounting torque: 1.5 Nm / Empfohlenes Drehmoment: 1.5 Nm





Rectifier

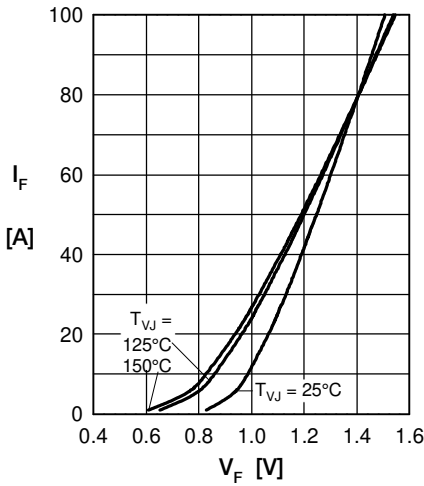


Fig. 1 Forward current vs. voltage drop per diode

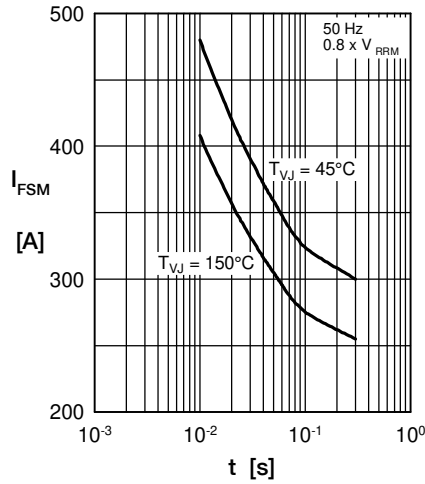


Fig. 2 Surge overload current vs. time per diode

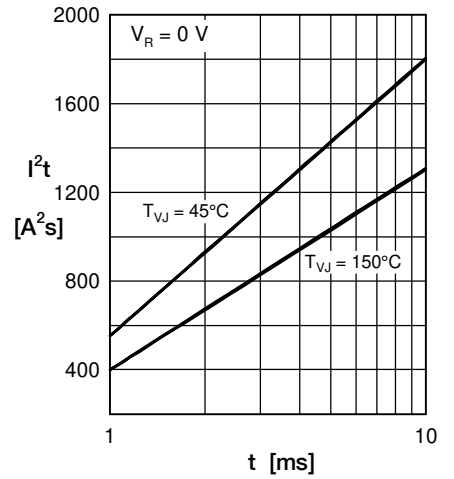


Fig. 3 I^2t vs. time per diode

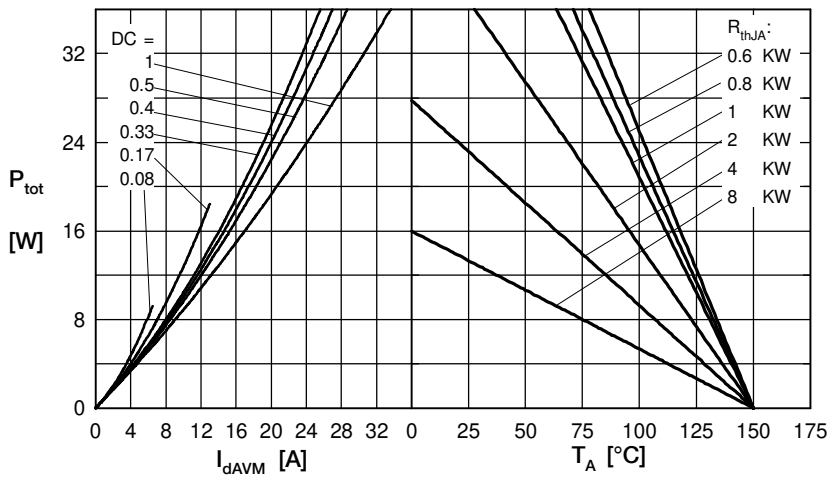


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

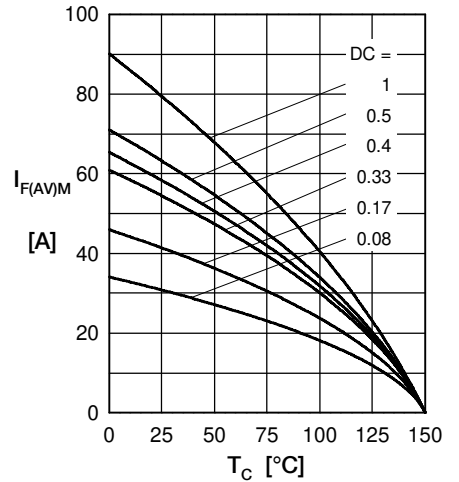


Fig. 5 Max. forward current vs. case temperature per diode

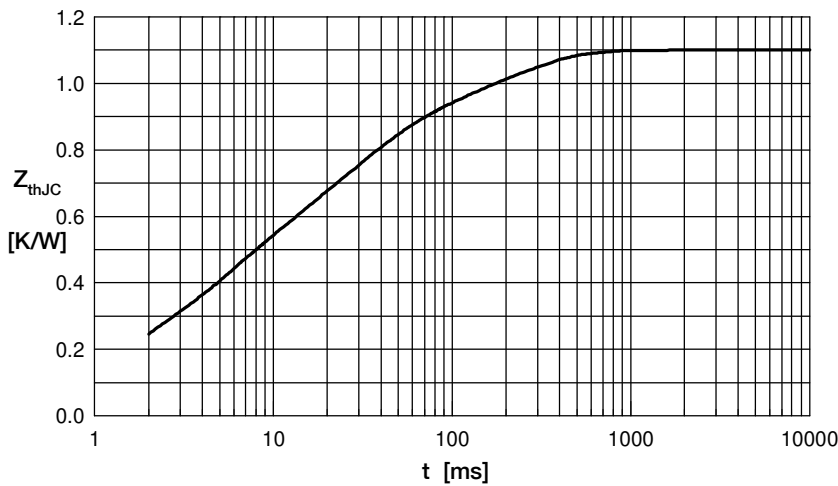


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.0607	0.0004
2	0.1230	0.00256
3	0.2305	0.0045
4	0.4230	0.0242
5	0.2628	0.1800

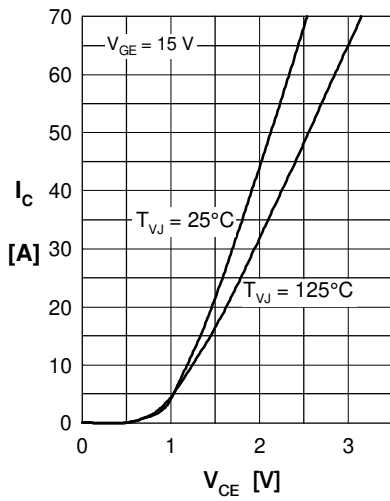
Brake IGBT


Fig. 1 Typ. output characteristics

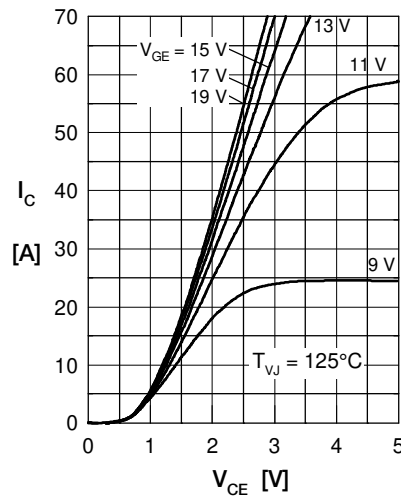


Fig. 2 Typ. output characteristics

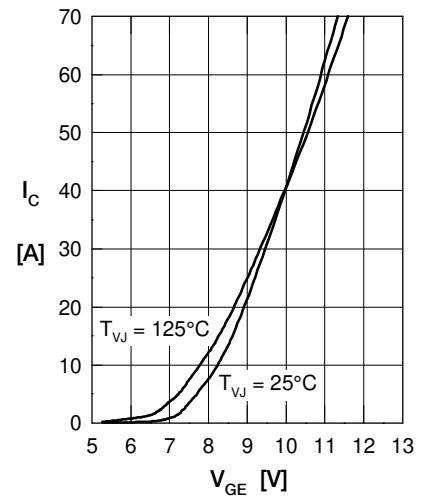


Fig. 3 Typ. transfer characteristics

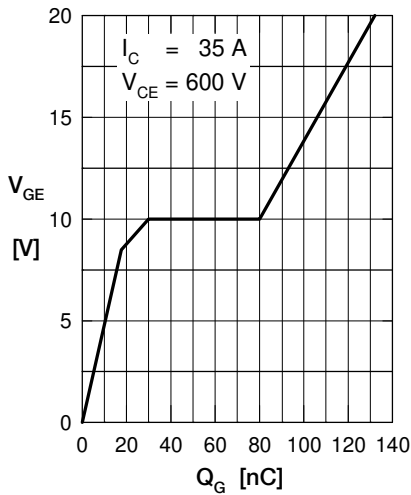


Fig. 4 Typ. turn-on gate charge

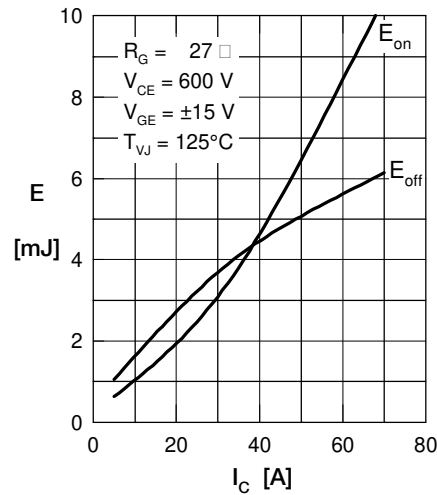


Fig. 5 Typ. switching energy versus collector current

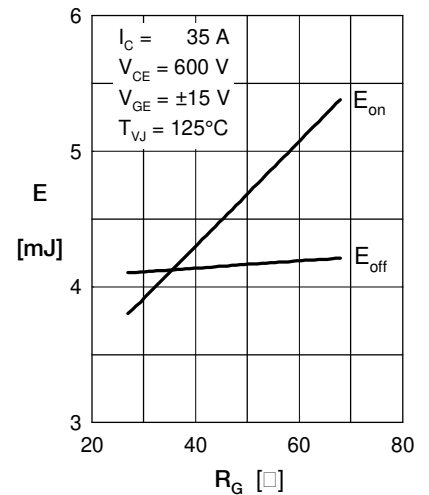


Fig. 6 Typ. switching energy versus gate resistance

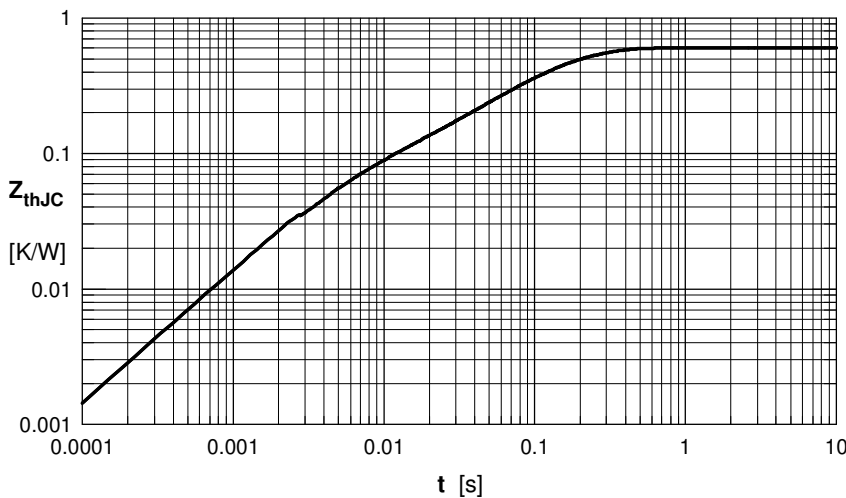


Fig. 7 Typ. transient thermal impedance

Brake Diode

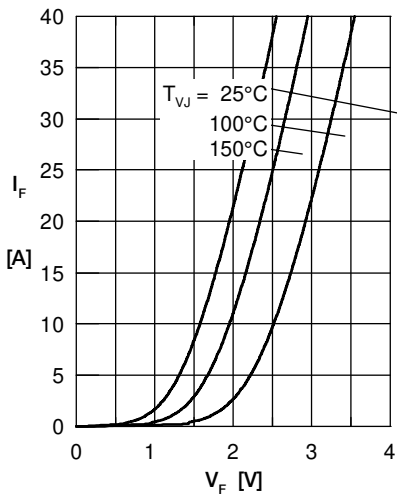


Fig. 1 Forward current I_F versus V_F

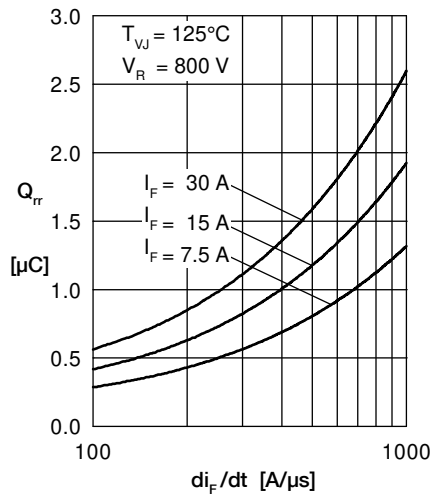


Fig. 2 Typ. reverse recov. charge Q_{rr} versus di_F/dt

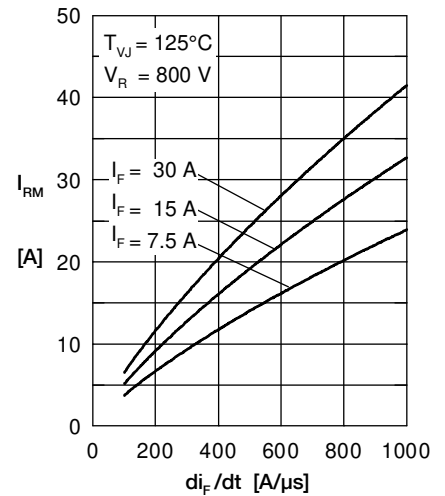


Fig. 3 Typ. peak reverse current I_{RM} versus di_F/dt

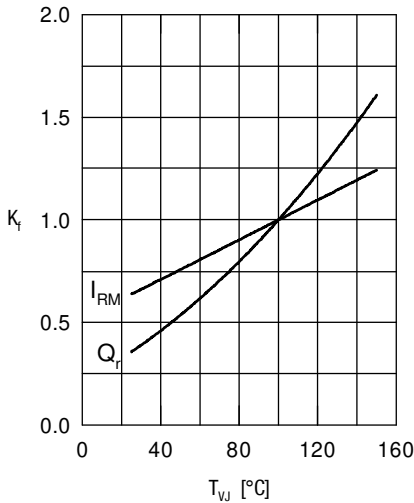


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

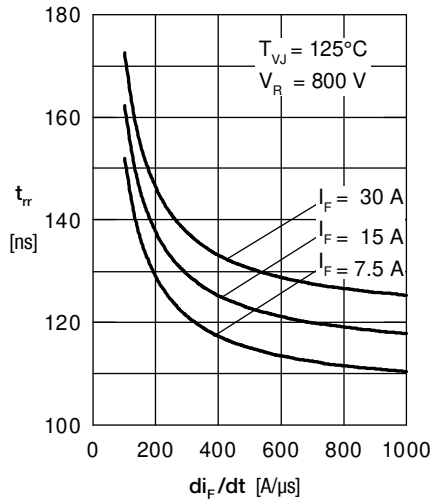


Fig. 5 Typ. recovery time t_{rr} versus di_F/dt

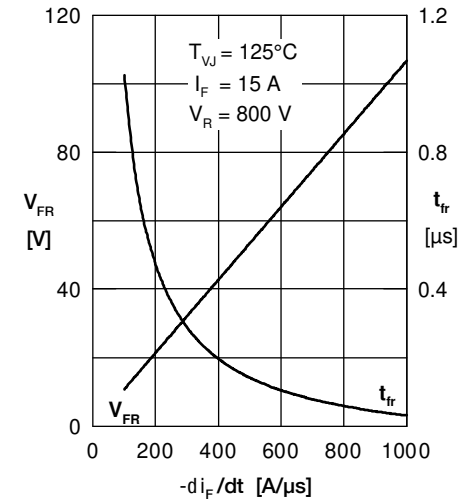


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

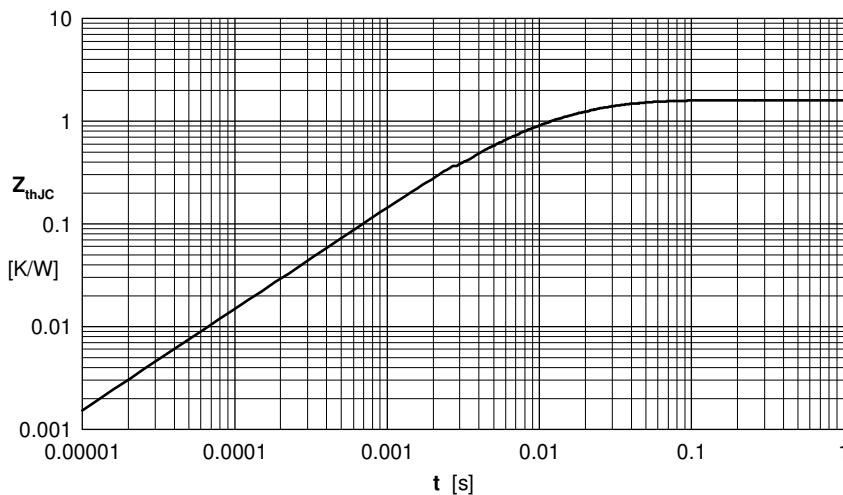


Fig. 7 Transient thermal impedance junction to case